BLC10G18XS-552AVT

Power LDMOS transistor

AMPLEON

Rev. 1 — 31 October 2019

Product data sheet

1. Product profile

1.1 General description

550 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 1880 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25$ °C in an asymmetrical Doherty demo circuit. $V_{DS} = 30$ V; $I_{Dq} = 950$ mA (main); $V_{GS(amp)peak} = 1.1$ V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η _D	ACPR
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	30	49.5	16.8	48.3	-32.1 ^[1]

Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1880 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain2 (peak)			
2	drain1 (main)		7 2 1 6	2, 7
3	gate1 (main)		5	
4	gate2 (peak)		3 4	5
5	source	[1]		4—
6	video decoupling (peak)			' ⊢ ¬
7	video decoupling (main)			1, 6 aaa-014884

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	Description	Version		
BLC10G18XS-552AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-4		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V _{GS(amp)main}	main amplifier gate-source voltage		-6	+9	V
V _{GS(amp)peak}	peak amplifier gate-source voltage		-6	+9	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T _{case}	case temperature	operating [1]	-40	+125	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	V_{DS} = 30 V; I_{Dq} = 950 mA (main); $V_{GS(amp)peak}$ = 1.03 V; T_{case} = 80 °C		
		P _L = 115 W	0.21	k/W
		P _L = 145 W	0.19	k/W

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6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.8 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 180 \text{ mA}$	1.6	2.0	2.4	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 30 \text{ V}; I_D = 950 \text{ mA}$	-	2.1	-	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	34	-	A
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V	-	-	280	nA
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 9.0 \text{ A}$	-	20.5	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 6.3 \text{ A}$	-	72	108	mΩ
Peak dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.8 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 380 \text{ mA}$	1.6	2.0	2.4	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 30 \text{ V}; I_D = 1900 \text{ mA}$	-	2.1	-	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	57	-	A
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V	-	-	280	nΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 19.0 \text{ A}$	-	39	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 13.3 \text{ A}$	-	37	62	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 64 DPCH; f_1 = 1807.5 MHz; f_2 = 1877.5 MHz; RF performance at V_{DS} = 30 V; I_{Dq} = 950 mA (main); $V_{GS(amp)peak}$ = 1.13 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 115 W	15.1	16.1	-	dB
RLin	input return loss	P _{L(AV)} = 115 W	-	-13	-8	dB
η_{D}	drain efficiency	P _{L(AV)} = 115 W	44	48	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 115 W	-	-33	-28	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 64 DPCH; f = 1877.5 MHz; RF performance at $V_{DS} = 30$ V; $I_{Dq} = 950$ mA (main); $V_{GS(amp)peak} = 1.13$ V; $T_{case} = 25$ °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at a frequency of 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P _{L(AV)} = 148 W	6.3	6.8	-	dB
$P_{L(M)}$	peak output power	P _{L(AV)} = 148 W	620	705	-	W

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7. Test information

7.1 Ruggedness in Doherty operation

The BLC10G18XS-552AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 30 V; I_{Dq} = 800 mA; $V_{GS(amp)peak}$ = 1.15 V; f = 1805 MHz; P_L = 235 W (5 dB OBO); 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; $I_{Dq} = 1$ A (main); $V_{DS} = 30$ V; pulsed CW ($t_p = 100 \ \mu s$; $\delta = 10 \ \%$).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]			
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)			
Maximum	Maximum power load							
1810	2.6 – j6.6	1.8 – j3.1	285.36	61.99	16.39			
1845	3.5 – j7.3	1.5 – j3.1	286.73	59.31	16.25			
1880	4.6 – j7.8	1.6 – j3.2	281.16	60.32	16.41			
Maximum	drain efficiency	load						
1810	2.6 – j6.6	3.2 – j2.2	203.39	68.8	18.26			
1845	3.5 – j7.3	3.0 – j1.5	180.88	68.43	18.81			
1880	4.6 – j7.8	2.7 – j2.0	199.61	68.01	18.48			

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

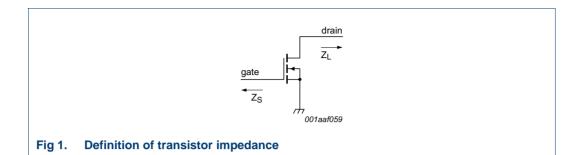
Measured load-pull data of peak device; $I_{Dq} = 1.9$ A (peak); $V_{DS} = 30$ V; pulsed CW ($t_p = 100 \ \mu s$; $\delta = 10$ %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]			
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)			
Maximum	Maximum power load							
1810	2.2 – j4.5	1.5 – j2.9	550.81	59.45	16.7			
1845	3.3 – j4.0	1.5 – j2.9	541	59.25	17.05			
1880	4.0 – j3.5	1.6 – j2.8	529.9	60.76	17.6			
Maximum	n drain efficiency	load						
1810	2.2 – j4.5	2.1 – j1.6	393.5	67.11	18.76			
1845	3.3 – j4.0	1.5 – j1.6	366.31	65.83	19.35			
1880	4.0 – j3.5	1.5 – j1.7	372.09	65.86	19.54			

^[1] Z_S and Z_L defined in Figure 1.

^[2] At 3 dB gain compression.

^[2] At 3 dB gain compression.



7.3 Test circuit

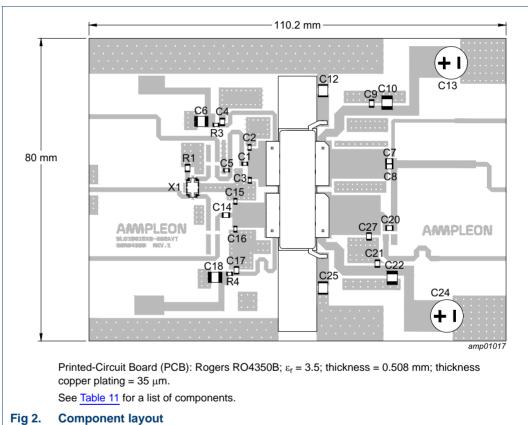


Table 11. List of components See Figure 2 for component layout.

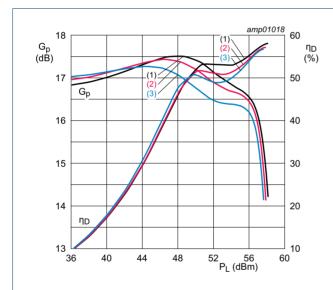
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1.8 pF	GQM18
C2, C3	multilayer ceramic chip capacitor	1.0 pF	GQM18
C4, C9, C14, C17, C21	multilayer ceramic chip capacitor	18 pF	GQM21
C5	multilayer ceramic chip capacitor	1.8 pF	GQM21
C6, C10, C12, C18, C22, C25	electrolytic capacitor	4.7 μF, 50 V	Murata: X7R
C7, C8	multilayer ceramic chip capacitor	8.2 pF	GQM21
C11, C19, C23, C26	multilayer ceramic chip capacitor		not mounted

Table 11. List of components ...continued See Figure 2 for component layout.

Component	Description	Value	Remarks
C13, C24	multilayer ceramic chip capacitor	470 μF, 63 V	Elco
C15, C16	multilayer ceramic chip capacitor	1.8 pF	GQM21
C20	multilayer ceramic chip capacitor	10 pF	GQM21
C27	multilayer ceramic chip capacitor	0.4 pF	GQM21
R1	resistor	50 Ω	Anaren: C16A50Z4
R2	resistor		not mounted
R3, R4	resistor	5.1 Ω	
X1	hybrid coupler		Anaren: X3C20F1-02S

7.4 Graphical data

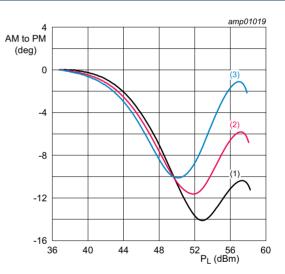
7.4.1 Pulsed CW



 V_{DS} = 30 V; I_{Dq} = 950 mA; $V_{GS(amp)peak}$ = 1.10 V; t_{D} = 100 $\mu s; \, \delta$ = 10 %.

- (1) f = 1805 MHz
- (2) f = 1845 MHz
- (3) f = 1880 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



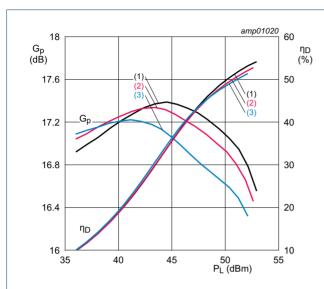
 $V_{DS}=30$ V; $I_{Dq}=950$ mA; $V_{GS(amp)peak}=1.10$ V; $t_{p}=100~\mu s;~\delta=10~\%.$

- (1) f = 1805 MHz
- (2) f = 1845 MHz
- (3) f = 1880 MHz

Fig 4. Normalized AM to PM as a function of output power; typical values

7.4.2 1-Carrier W-CDMA

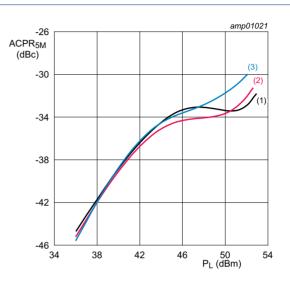
Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.



 $V_{DS} = 30 \text{ V}$; $I_{Dq} = 950 \text{ mA}$; $V_{GS(amp)peak} = 1.10 \text{ V}$.

- (1) f = 1805 MHz
- (2) f = 1845 MHz
- (3) f = 1880 MHz

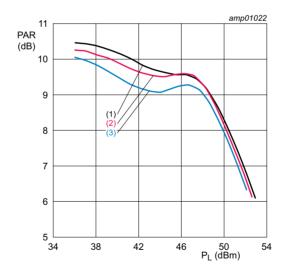
Fig 5. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 30 \text{ V}; I_{Dq} = 950 \text{ mA}; V_{GS(amp)peak} = 1.10 \text{ V}.$

- (1) f = 1805 MHz
- (2) f = 1845 MHz
- (3) f = 1880 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

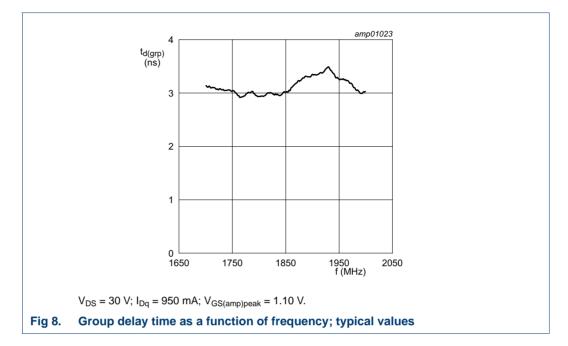


 $V_{DS} = 30 \text{ V}; I_{Dq} = 950 \text{ mA}; V_{GS(amp)peak} = 1.10 \text{ V}.$

- (1) f = 1805 MHz
- (2) f = 1845 MHz
- (3) f = 1880 MHz

Fig 7. Peak-to-average power ratio as a function of output power; typical values

7.4.3 Group delay



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8. Package outline

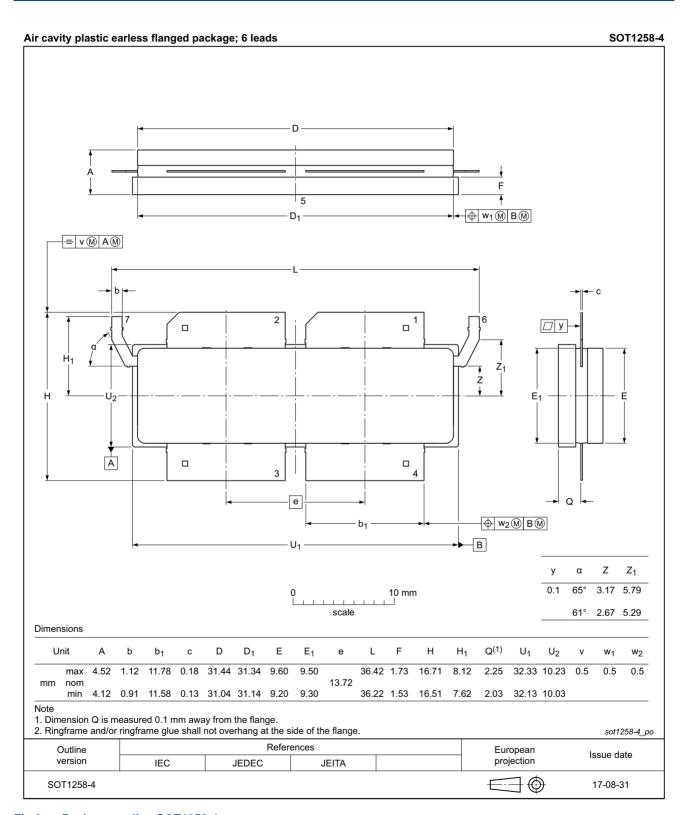


Fig 9. Package outline SOT1258-4

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 13. Abbreviations

Acronym	Description		
3GPP	3rd Generation Partnership Project		
AM	Amplitude Modulation		
CCDF	Complementary Cumulative Distribution Function		
CW	Continuous Wave		
DPCH	Dedicated Physical CHannel		
ESD	ElectroStatic Discharge		
LDMOS	Laterally Diffused Metal-Oxide Semiconductor		
MTF	Median Time to Failure		
ОВО	Output Back Off		
PAR	Peak-to-Average Ratio		
PM	Phase Modulation		
RoHS	Restriction of Hazardous Substances		
VSWR	Voltage Standing Wave Ratio		
W-CDMA	Wideband Code Division Multiple Access		

11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC10G18XS-552AVT v.1	20191031	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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